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Substitute for form 1449A/B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	of	11	Attorney Docket Number	Complete if Known
				Application Number	09/940,792-Conf.#5268
				Filing Date	August 29, 2001
				First Named Inventor	Paul A. Farrar et al.
				Art Unit	2815
				Examiner Name	E.C.H. Lee
					M4065.0382/P382-A

CLASS 610 CLASS 5

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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BA	EP 1030196		08/2000			
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
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Sheet	6	of	11	Attorney Docket Number	M4065.0382/P382-A

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Substitute for form 1449A/B/PTO				Complete If Known	
				Application Number	09/940,792-Conf.#5268
				Filing Date	August 29, 2001
				First Named Inventor	Paul A. Farrar et al.
				Art Unit	2815
				Examiner Name	E.C.H. Lee
Sheet	8	of	11	Attorney Docket Number	M4065.0382/P382-A

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Examiner Signature

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				Examiner Name	E.C.H. Lee
Sheet	9	of	11	Attorney Docket Number	M4065.0382/P382-A

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Examiner Signature	Date Considered
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Complete if Known

Application Number	09/940,792-Conf.#5268
Filing Date	August 29, 2001
First Named Inventor	Paul A. Farrar et al.
Art Unit	2815
Examiner Name	E.C.H. Lee

Attorney Docket Number M4065.0382/P382-A

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 11 of 11*Complete if Known*

Application Number	09/940,792-Conf.#5268
Filing Date	August 29, 2001
First Named Inventor	Paul A. Farrar et al.
Art Unit	2815
Examiner Name	E.C.H. Lee
Attorney Docket Number	M4065.0382/P382-A

<i>el</i>	CX4	Lasers and Electro-Optics Soc., Conf. Proc., Nov 10-13, 1996, 31.
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¹EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		Complete if Known 09/940792	
Application Number	Not Yet Assigned		
Filing Date	August 29, 2001		
First Named Inventor	Paul A. Farrar		
Group Art Unit	2812-2815		
Examiner Name	D. Zarneske Lee		
	JCCS86 09/940792 08/29/01		
	U.S. PTO		
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U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U. S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
W	A	5,920,121		Forbes, et al.*	07/06/1999	
KL	B	6,100,176		Forbes, et al.*	08/08/2000	
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GL	A	5,963,838		Yamamoto et al.	10/15/1999

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Attorney Docket Number	M4065.0382/P382-A

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Examiner Initials	Cite No. ¹	
GL	B	F.A. Nichols, et al. - "Surface- (Interface-) and Volume-Diffusion Contributions to Morphological Changes Driven by Capillarity," Transactions of the Metallurgical Society of AIME, Volume 233, October 1965, pgs. 1840-1848*
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GL	D	U.S. Application, Serial No. 09/069,346 filed April 29, 1998, Attorney docket #303.367US1, pgs. 1-22 w/6 shts. drwgs.*

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